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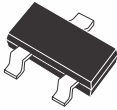
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Central Semiconductor Corp.



CMPTA29

**HIGH VOLTAGE
NPN SILICON
DARLINGTON TRANSISTOR**



SOT-23 CASE

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPTA29 is a Silicon NPN Darlington Transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for applications requiring extremely high voltage and high gain.

Marking Code is C29.

MAXIMUM RATINGS: (T_A=25°C)

	SYMBOL		UNITS
Collector-Base Voltage	V _{CBO}	100	V
Collector-Emitter Voltage	V _{CES}	100	V
Emitter-Base Voltage	V _{EBO}	12	V
Collector Current	I _C	500	mA
Power Dissipation	P _D	350	mW
Operating and Storage			
Junction Temperature	T _J , T _{stg}	-65 to +150	°C
Thermal Resistance	Θ _{JA}	357	°C/W

ELECTRICAL CHARACTERISTICS: (T_A=25°C)

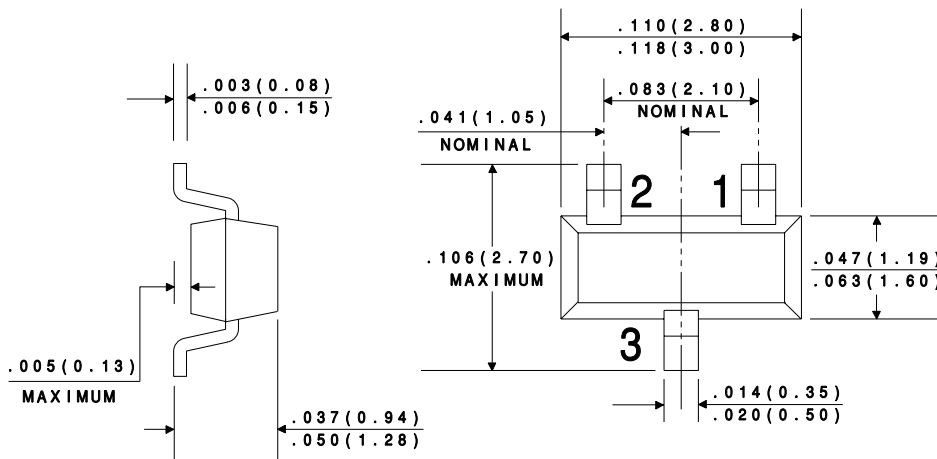
SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I _{CES}	V _{CE} =80V		500	nA
I _{CBO}	V _{CB} =80V		100	nA
I _{EBO}	V _{BE} =10V		100	nA
BV _{CES}	I _C =100μA	100		V
BV _{CBO}	I _C =100μA	100		V
BV _{EBO}	I _E =10μA	12		V
V _{CE(SAT)}	I _C =10mA, I _B =10μA		1.2	V
V _{CE(SAT)}	I _C =100mA, I _B =100mA		1.5	V
V _{BE(ON)}	V _{CE} =5.0V, I _C =100mA		2.0	V



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SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
h_{FE}	$V_{CE}=5.0V, I_C=10mA$	10,000		
h_{FE}	$V_{CE}=5.0V, I_C=100mA$	10,000		
f_T	$V_{CE}=5.0V, I_C=10mA, f=100MHz$	125		MHz
C_{ob}	$V_{CB}=10V, I_E=0, f=1.0MHz$		8.0	pF

All dimensions in inches (mm).



LEAD CODE:

- 1) BASE
- 2) EMITTER
- 3) COLLECTOR